

N-channel 30 V 7.1 mΩ logic level MOSFET in LFPAK using NextPower technology

Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 20 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.5	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 20 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{ see } \underline{\text{Figure } 14};$ $\text{see } \underline{\text{Figure } 15}$	-	7.9	-	nC

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb	
3	S	source		
4	G	gate	9	
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \end{array} \begin{array}{c} 2 \end{array} \begin{array}{c} 3 \end{array} \begin{array}{c} 4 \end{array}$	mbb076 S
			SOT669 (LFPAK; Power-SO8)	

3. Ordering information

Table 3. Or	. Ordering information				
Type number	r	Package			
		Name	Description	Version	
PSMN7R0-30	YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669	



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4. Limiting values

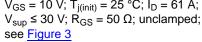
Table 4. Limiting values

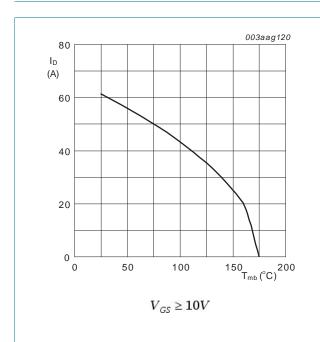
In accordance with the Absolute Maximum Rating System (IEC 60134).

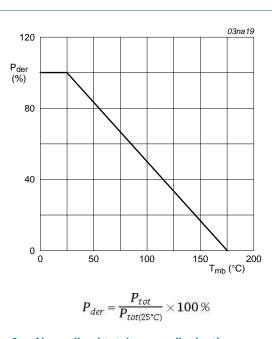
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	61	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	43	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	245	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	48	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	190	-	V
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	44	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	245	А
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source	V _{GS} = 10 V; T _{i(init)} = 25 °C; I _D = 61 A;	-	15	mJ

EDS(AL)S

avalanche energy



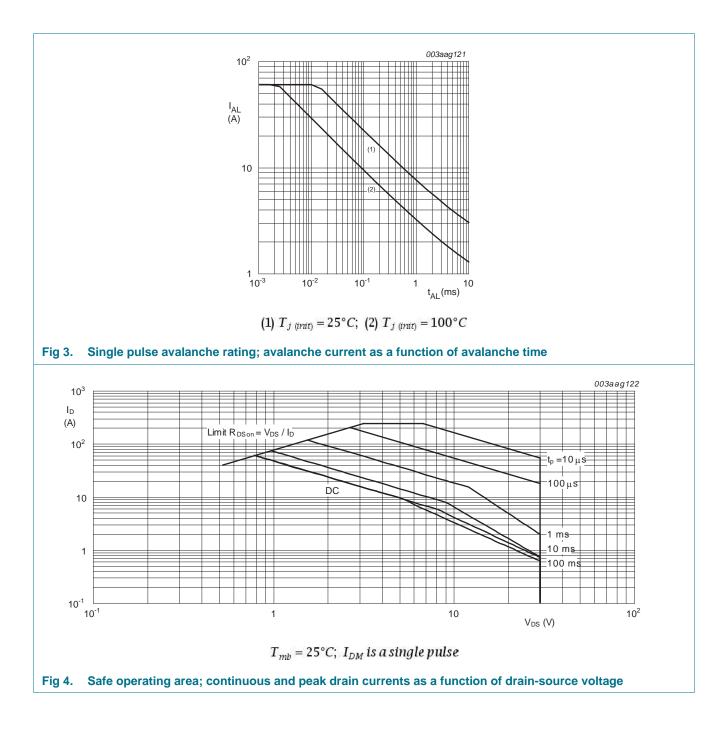








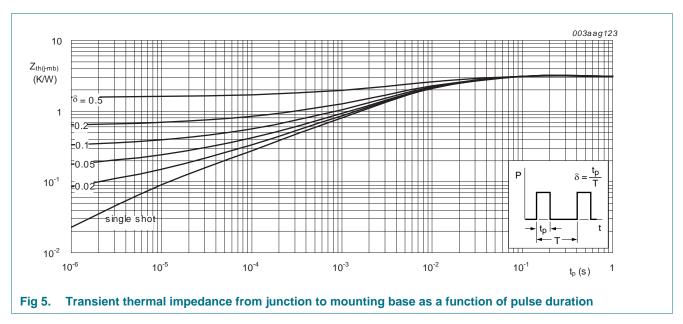
PSMN7R0-30YLC



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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	2.9	3.13	K/W



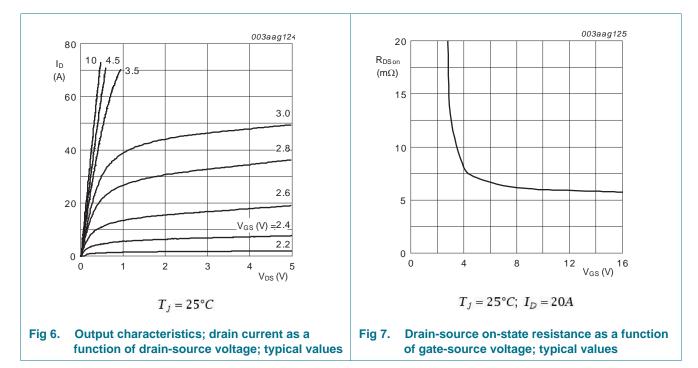
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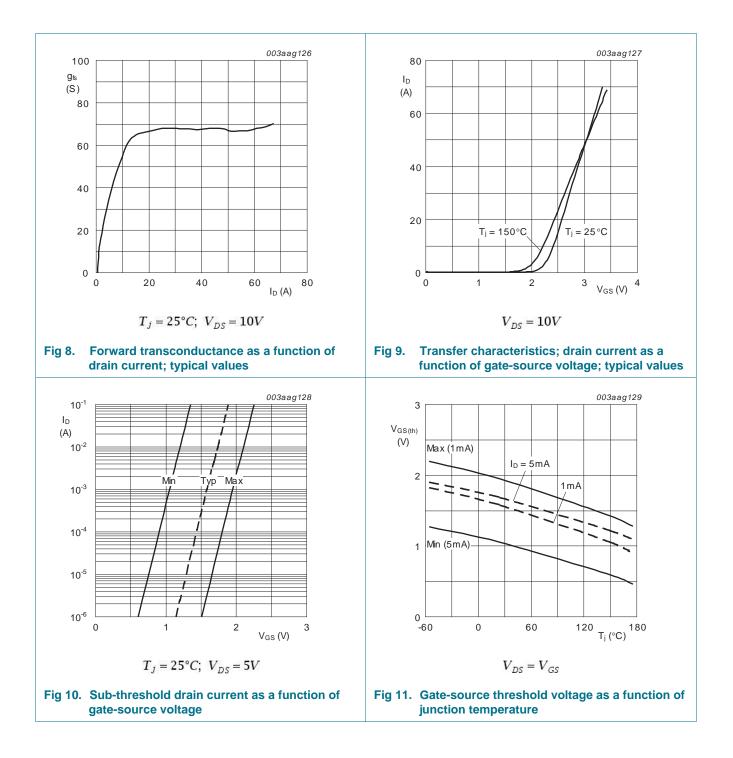
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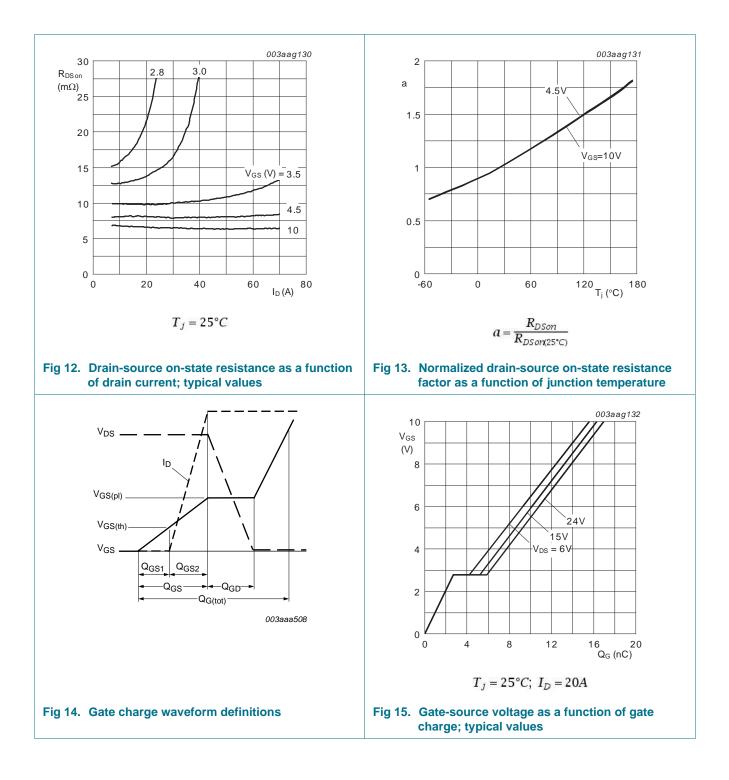
6. Characteristics

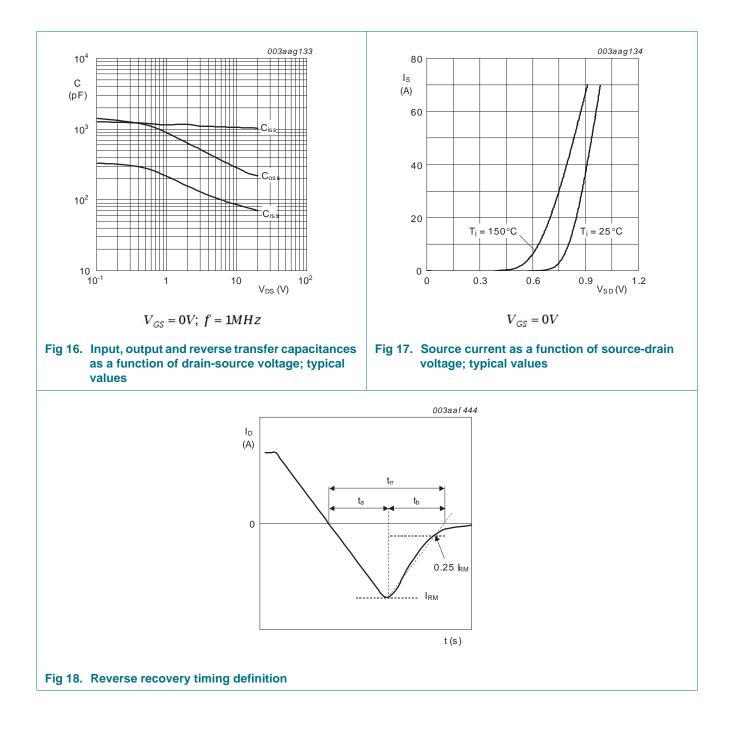
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 10</u>	1.05	1.58	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see Figure 11	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	2.35	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 20 A; T _j = 25 °C; see <u>Figure 12</u>	-	7.6	8.9	mΩ
		V_{GS} = 4.5 V; I_D = 20 A; T_j = 150 °C; see Figure 12; see Figure 13	-	-	14.7	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; see <u>Figure 12</u>	-	6	7.1	mΩ
		V_{GS} = 10 V; I_D = 20 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	- 1	11.8	mΩ
R _G	gate resistance	f = 1 MHz	-	2.2	4.4	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	16	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	7.9	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V;$ see <u>Figure 15</u>	-	14 -	-	nC
Q _{GS}	gate-source charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2.7	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	1.7	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1	-	nC
Q _{GD}	gate-drain charge		-	2.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.77	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	1057	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	235	-	pF
C _{rss}	reverse transfer capacitance		-	77	-	pF

Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; \text{ R}_{L} = 0.75 \ \Omega; \text{ V}_{GS} = 4.5 \text{ V};$	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	18	-	ns
t _{d(off)}	turn-off delay time		-	20	-	ns
t _f	fall time		-	7.5	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	6.4	-	nC
Source-dr	ain diode					
V _{SD}	source-drain voltage	I _S = 20 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.86	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	25	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	13	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 V; I_S = 20 A;$	-	16	-	ns
t _b	reverse recovery fall time	dl _S /dt = -100 A/µs; V _{DS} = 15 V; see <u>Figure 18</u>	-	9	-	ns









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7. Package outline

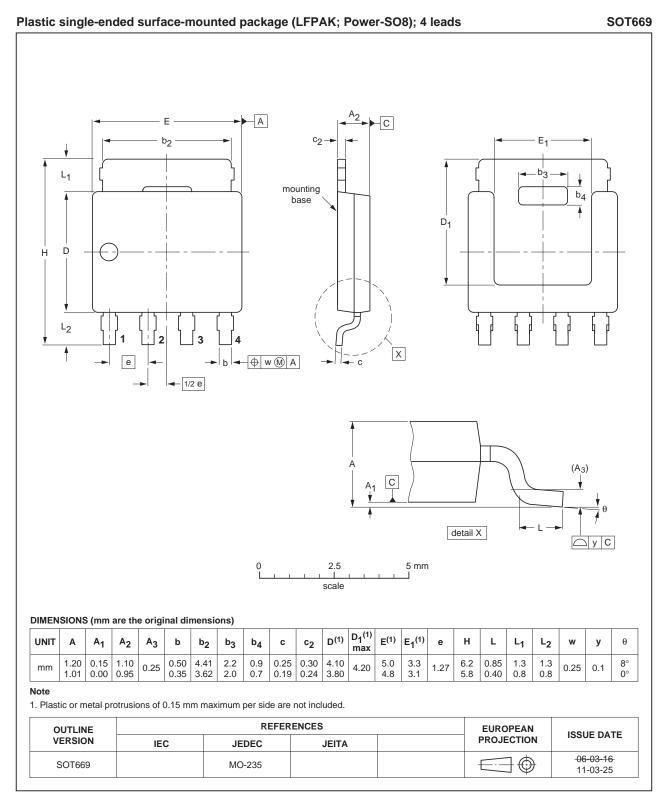


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7.Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-30YLC v.2	20110901	Product data sheet	-	PSMN7R0-30YLC v.1
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	es to content.		
PSMN7R0-30YLC v.1	20110711	Objective data sheet	-	-

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9. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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